



PATENT ABSTRACTS OF JAPAN

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ADACHI KAZUHIRO
ISHI TAKEMOTO**(54) **CELL STRUCTURE OF CMOS
SEMICONDUCTOR INTEGRATED CIRCUIT AND
DESIGN SYSTEM OF SEMICONDUCTOR
INTEGRATED CIRCUIT**

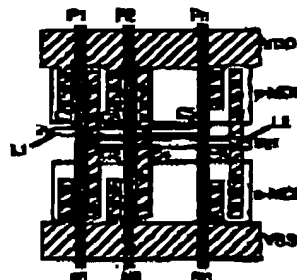
double-power inverter. And if contacts are arranged at C1-C6, it becomes an n-fold power inverter.

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(57) Abstract

PROBLEM TO BE SOLVED: To change only the driving force of a cell without changing the arrangement of the cell and the wiring between the cell terminals.

SOLUTION: (in) is an input terminal of a cell, (out) an output terminal of the cell, P1-Pn n units of p-MOS Trs arranged in parallel, and N1-Nn n units of n-MOS Trs arranged in parallel. P-MOS Trs and n-MOS Trs arranged in the longitudinal direction in the same lines constitute CMOS inverters respectively. L1 is wiring arranged in a cell for connecting the input terminals of n units of CMOS inverters in parallel mutually, and L2 is wiring for connecting the output terminals in parallel mutually. Concerning to the fundamental structure of the cell, any contact is not arranged at points C1-C6 proposed for arranging contacts. If contacts are arranged at the points C1, C2 proposed for contacts, the inverter becomes a mono-power one. If contacts are arranged at C1-C4, it becomes a



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